

# Keshuang Li

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/10461492/publications.pdf>

Version: 2024-02-01

8  
papers

105  
citations

1684188

5  
h-index

1872680

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g-index

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8  
docs citations

8  
times ranked

118  
citing authors

#	ARTICLE	IF	CITATIONS
1	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (001) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.	1.5	31
2	All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.	2.8	23
3	Inversion Boundary Annihilation in GaAs Monolithically Grown on On-axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.	7.3	22
4	Thin Ge buffer layer on silicon for integration of III-V on silicon. Journal of Crystal Growth, 2019, 514, 109-113.	1.5	17
5	The role of different types of dopants in 1.3 $\mu$ m InAs/GaAs quantum-dot lasers. Journal Physics D: Applied Physics, 2022, 55, 215105.	2.8	6
6	Impact of ex-situ annealing on strain and composition of MBE grown GeSn. Journal Physics D: Applied Physics, 2020, 53, 485104.	2.8	4
7	InAs/GaAs Quantum Dot Lasers Monolithically Integrated on Group IV Platform. , 2018, , .		1
8	GaAs Compounds Heteroepitaxy on Silicon for Opto and Nano Electronic Applications. , 0, , .		1